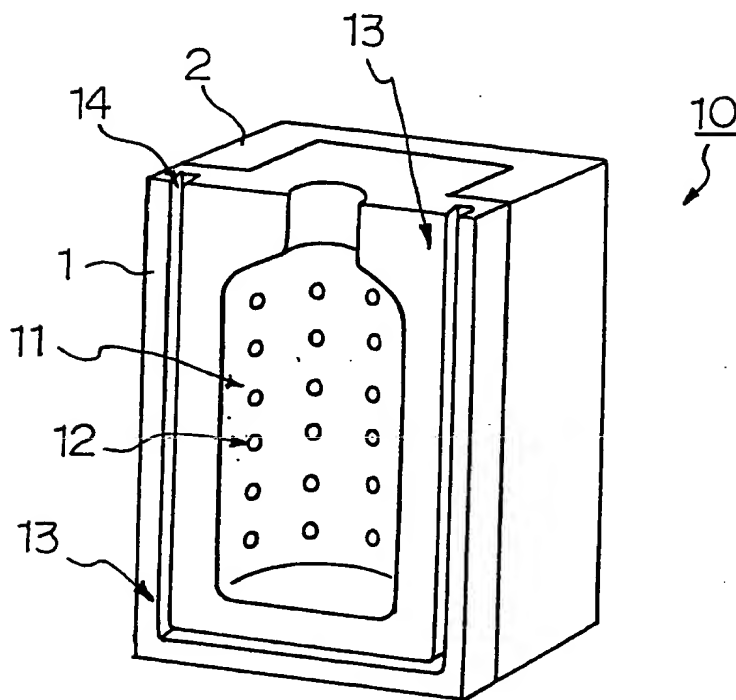


*Fig. 1*



*Fig. 2*

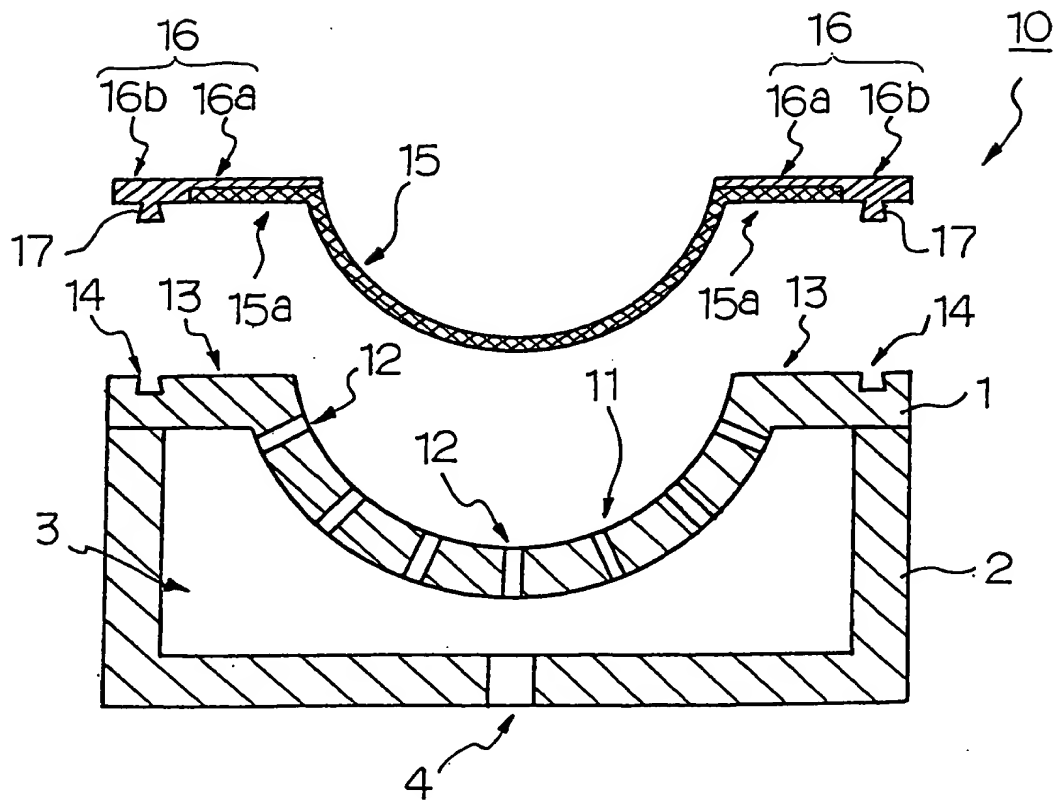




Fig. 3 (a)

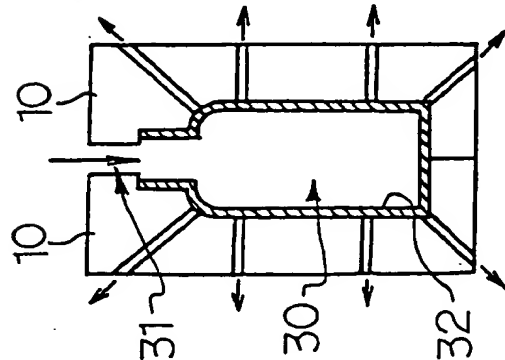


Fig. 3 (b)

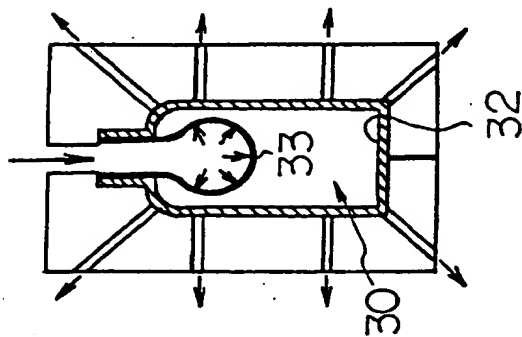


Fig. 3 (c)

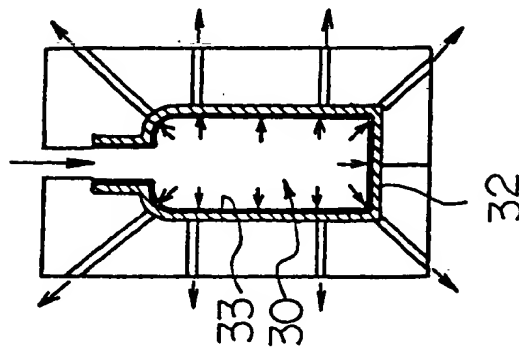


Fig. 3 (d)

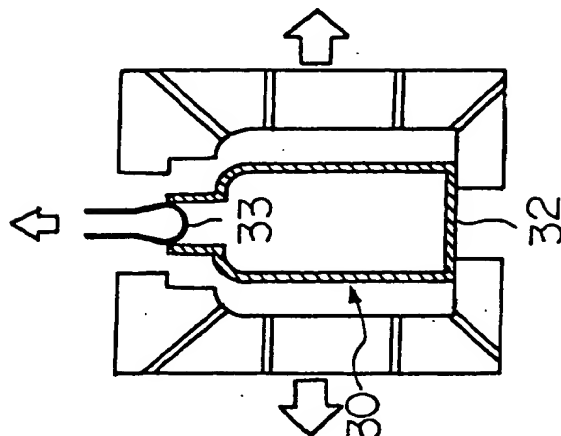
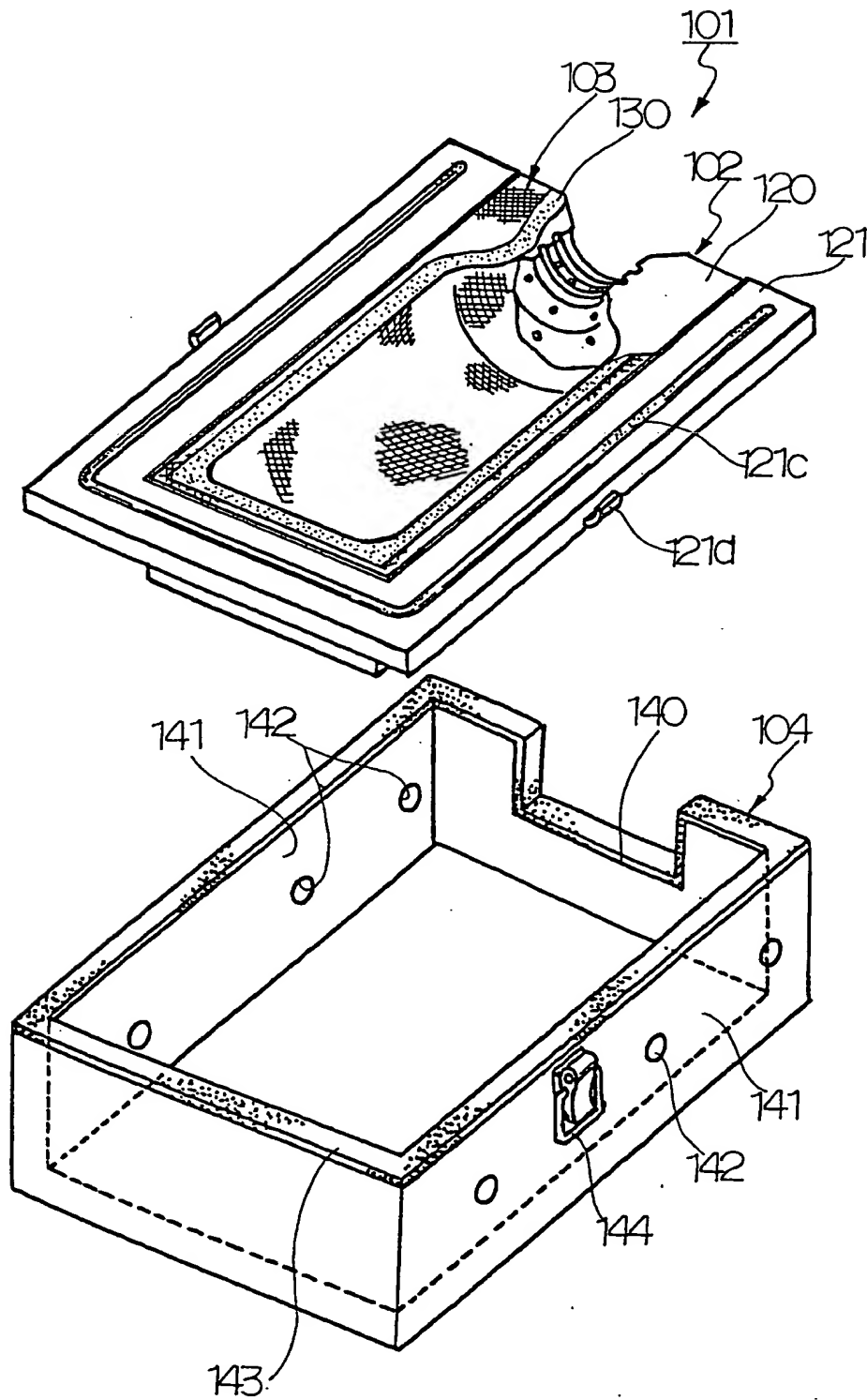


Fig. 4





*Fig. 5*

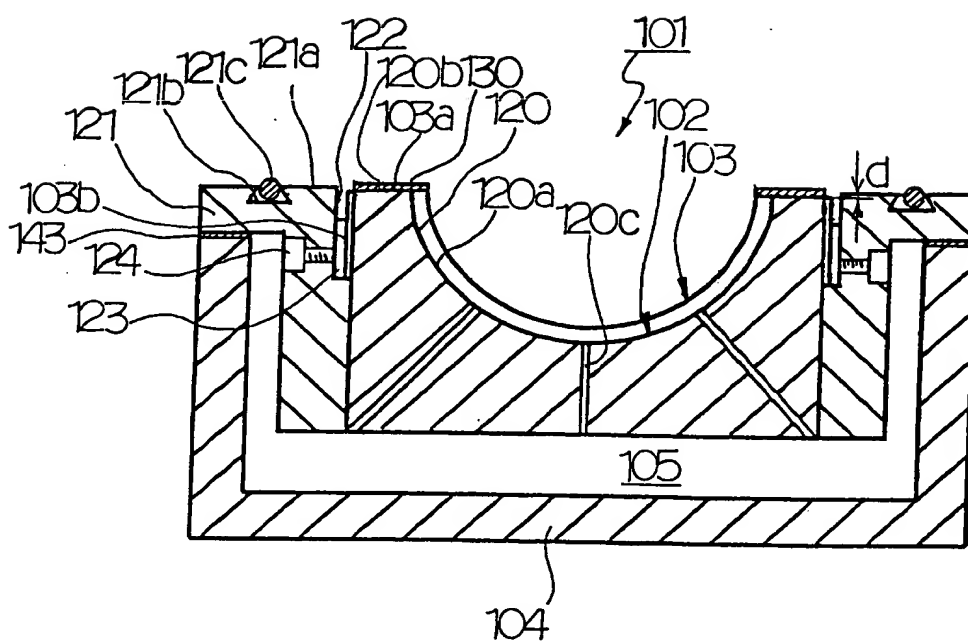


Fig. 6 (a)

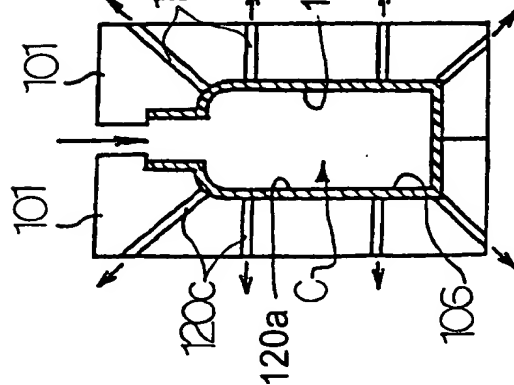


Fig. 6 (b)

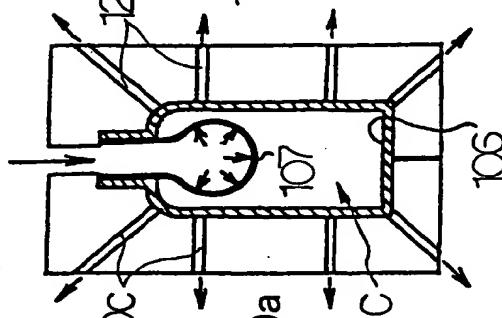


Fig. 6 (c)

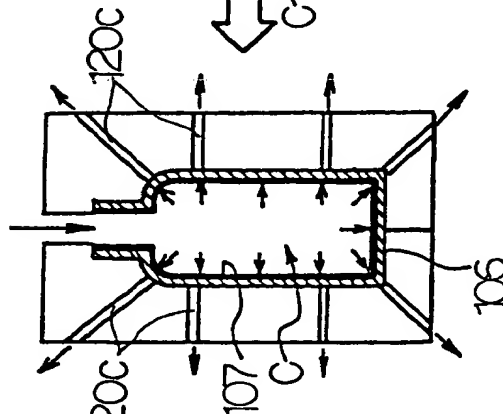
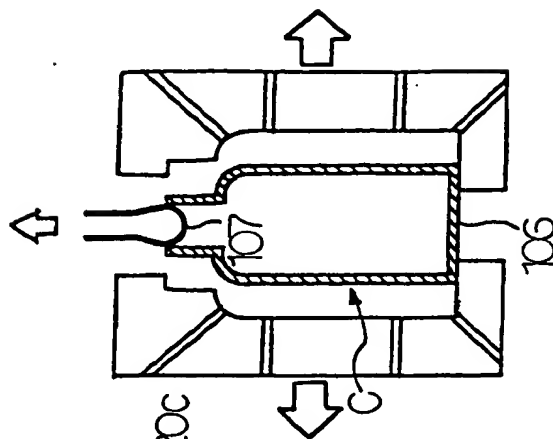


Fig. 6 (d)



[illegible]

Fig. 10 is a cross-sectional view of a semiconductor device. It shows a substrate 104 with a trench 105. A curved layer 120 is formed on the trench walls, with regions 120a, 120b, and 120c. A layer 101' is on top of the trench, with regions 101, 102, and 103. Various other layers and structures are labeled with numbers 121 through 143.

*Fig. 11*

